40 V, 200 mA PNP switching transistor
Rev. 1 — 2 April 2012

**Product data sheet** 

## **Product profile**

## 1.1 General description

PNP single switching transistor in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PMBT3904MB.

#### 1.2 Features and benefits

- Single general-purpose switching transistor
- AEC-Q101 qualified
- Ultra small SMD plastic package
- Board-space reduction
- Low package height of 0.37 mm

## 1.3 Applications

- General-purpose switching and amplification
- Mobile applications

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-40	V
$I_{C}$	collector current		-	-	-200	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = -1 \text{ V};$ $I_{C} = -10 \text{ mA}$	100	180	300	

## 2. Pinning information

Table 2. **Pinning** 

	3		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	1 3	3 
3	collector	2 🔲	1—
		Transparent	. ,
		top view	2
			sym013



## 3. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PMBT3906MB	DFN1006B-3	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.37$ mm	SOT883B

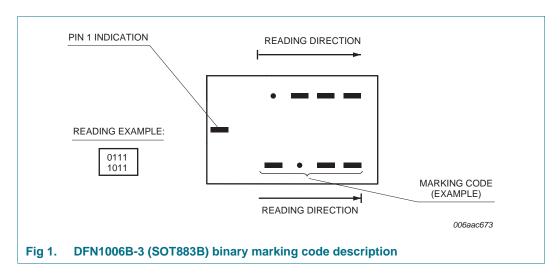
## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMBT3906MB	0100 1000

[1] For DFN1006B-3 (SOT883B) binary marking code description, see Figure 1.

## 4.1 Binary marking code description



## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		•	,		
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{CBO}}$	collector-base voltage	open emitter	-	-40	V
$V_{CEO}$	collector-emitter voltage	open base	-	-40	V
$V_{EBO}$	emitter-base voltage	open collector	-	-6	V
I <sub>C</sub>	collector current		-	-200	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1][2] _	250	mW
			[1][3]	590	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Reflow soldering is the only recommended soldering method.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

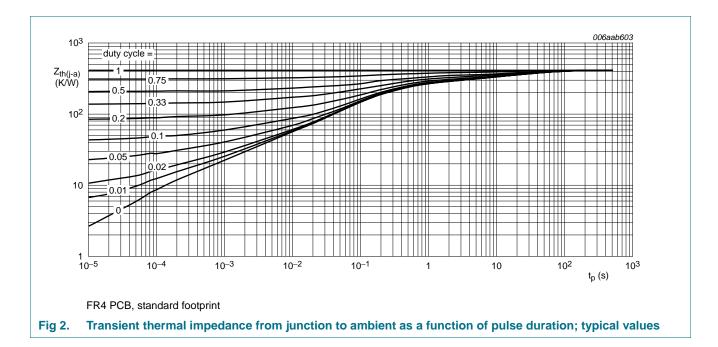
<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1][2]	-	500	K/W
	junction to ambient		[1][3]	-	212	K/W

- [1] Reflow soldering is the only recommended soldering method.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



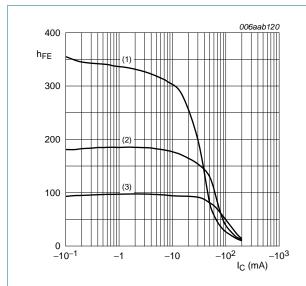
## 7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-50	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -6 \text{ V}; I_{C} = 0 \text{ A}$	-	-	-50	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -1 V$				
		$I_{C} = -0.1 \text{ mA}$	60	180	-	
		$I_C = -1 \text{ mA}$	80	180	-	
		$I_C = -10 \text{ mA}$	100	180	300	
		$I_C = -50 \text{ mA}$	60	130	-	
		$I_C = -100 \text{ mA}$	[1] 30	50	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-100	-250	mV
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-165	-400	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-750	-850	mV
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-850	-950	mV
t <sub>d</sub>	delay time	$V_{CC} = -3 \text{ V};$ $I_{C} = -10 \text{ mA};$	-	-	35	ns
t <sub>r</sub>	rise time		-	-	35	ns
t <sub>on</sub>	turn-on time	- I <sub>Bon</sub> = -1 mA; - I <sub>Boff</sub> = 1 mA	-	-	70	ns
t <sub>s</sub>	storage time	5011	-	-	225	ns
t <sub>f</sub>	fall time		-	-	75	ns
t <sub>off</sub>	turn-off time		-	-	300	ns
C <sub>c</sub>	collector capacitance	$V_{CB} = -5 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	4.5	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -500 \text{ mV};$ $I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$	-	-	10	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -20 \text{ V};$ $I_{C} = -10 \text{ mA};$ f = 100  MHz	250	-	-	MHz
NF	noise figure	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \text{ μA}; R_{S} = 1 \text{ k}\Omega;$ $f = 10 \text{ Hz to } 15.7 \text{ kHz}$	-	-	4	dB

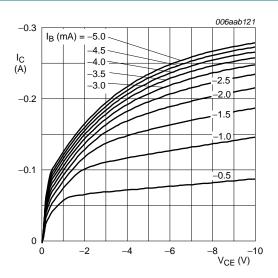
<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 



$$V_{CE} = -1 V$$

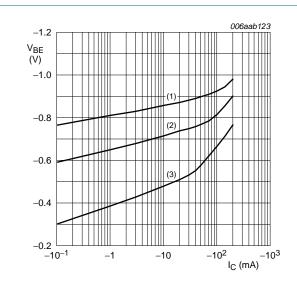
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 4. Collector current as a function of collector-emitter voltage; typical values



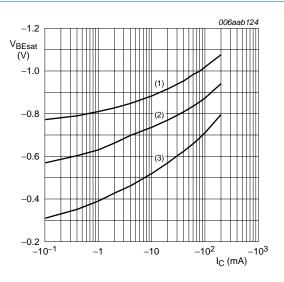
$$V_{CE} = -1 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 5. Base-emitter voltage as a function of collector current; typical values



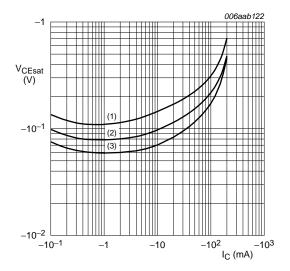
$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=10$$

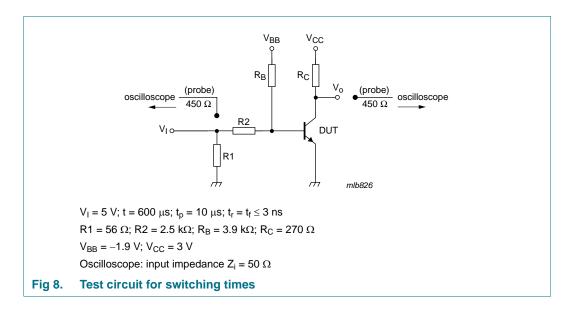
(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

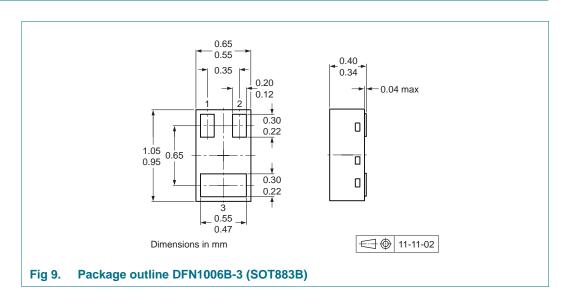
## 8. Test information



## Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 10. Package outline



## 11. Packing information

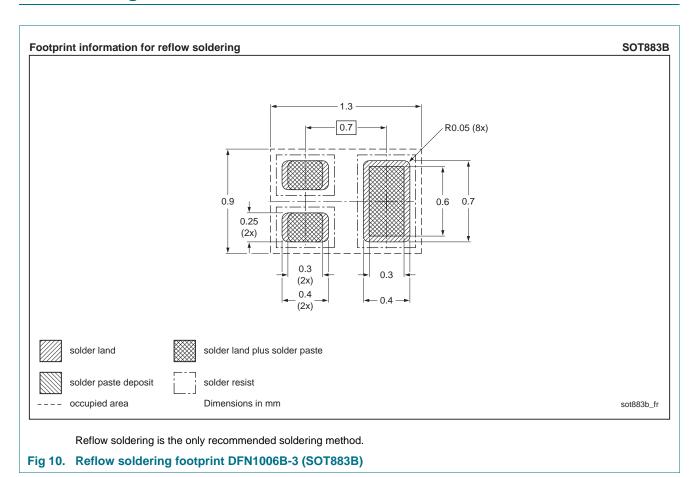
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity 10000
PMBT3906MB	DFN1006B-3 (SOT883B)	2 mm pitch, 8 mm tape and reel	-315

<sup>[1]</sup> For further information and the availability of packing methods, see Section 15.

## 12. Soldering



40 V, 200 mA PNP switching transistor

## 13. Revision history

## Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBT3906MB v.1	20120402	Product data sheet	-	-

## 14. Legal information

#### 14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### 40 V, 200 mA PNP switching transistor

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## 40 V, 200 mA PNP switching transistor

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